PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/685,251
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(use as many sheets as necessary)				Confirmation Number	Unknown
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	Unknown
				Examiner Name	Unknown
Sheet	1	of	9	Attorney Docket No.	MEMC 96-0055(2101.3)

U.S. PATENT & TRADEMARK OFFICE DEC 11 2003

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Sheet 2 of 9	Attorney Docket No.	MEMC 96-0055(2101.3)

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Sheet 3 of 9	Attorney Docket No.	MEMC 96-0055(2101.3)

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Sheet 4 of 9	Attorney Docket No.	MEMC 96-0055(2101.3)

U.S. PATENT & TRADEMARK OFFICE DEC 11 2003

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PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/685,251
				Filing Date	October 14, 2003
(use as many sheets as necessary)				Confirmation Number	Unknown
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	Unknown
				Examiner Name	Unknown
Sheet	9	of	9	Attorney Docket No.	MEMC 96-0055(2101.3)

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